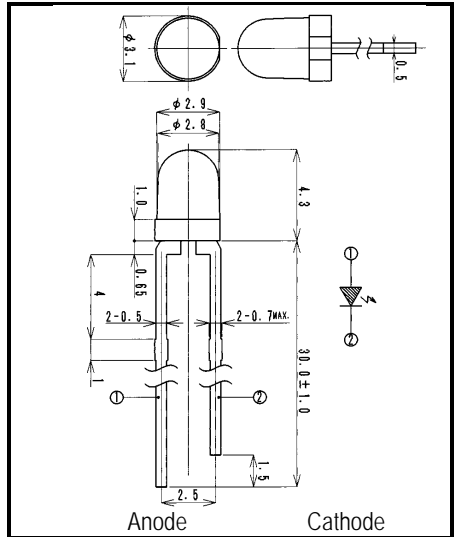


# LSF811C1

# Infrared Emitting Diode



- FEATURES
- High-output Power
  - Compact
  - High Reliability
- APPLICATIONS
- Optical Switches
  - Optical Sensors
  - Medical Application

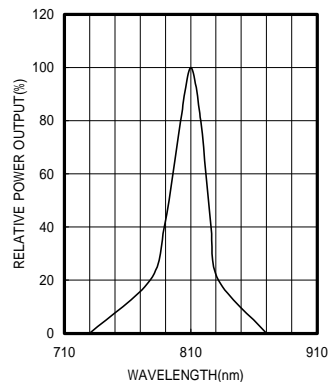
## 1. ABSOLUTE MAXIMUM RATINGS (Ta=25 °C)

ITEM	SYMBOL	RATINGS	UNIT
Forward Current (DC)	IF	60	mA
Forward Current (Pulse)*1	IFP	0.5	A
Reverse Voltage	VR	5	V
Power Dissipation	PD	120	mW
Operating Temp.	ToPr	-20 TO 85	
Storage Temp.	Tstg	-30 TO 100	
Junction Temp.	Tj	100	
Lead Soldering Temp.*2	Tls	260	

\*1:Tw=10uS,T=10mS

\*2:Time 5 Sec max,Position:Up to 3mm from the body

## SPECTRAL OUTPUT



To purchase this part contact  
Marktech Optoelectronics at

**800.984.5337**

 **Marktech**  
Optoelectronics

www.marktechopto.com



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# Infrared Emitting Diode

## 2.ELECTRICAL & OPTICAL CHARACTERISTICS (Ta=25 )

ITEM	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Power Output	PO	IF=20mA		6.5		mW
Forward Voltage	VF	IF=20mA		1.4	1.9	V
Reverse Current	IR	VR=5V			100	μA
Peak Wavelength	ρ	IF=20mA		810		nm
Spectral Line Half Width		IF=20mA		30		nm
Half Intensity Beam Angle		IF=20mA		±25		deg.
Rise Time	Tr	IFP=50mA		-		nS
Fall Time	Tf	IFP=50mA		-		nS
Junction Capacitance	Cj	1MHz , V=0V		60		pF
Temp. Coefficient of PO	P/T	IF=10mA		-0.6		%/
Temp. Coefficient of VF	V/T	IF=10mA		-2.0		mV/

